

**Black phosphorus hybrid film enabled by covalently chemical and spatial hierarchical-locking effect for flexible supercapacitors with 100% cycling stability**

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† Electronic supplementary information (ESI) available.

## **Experimental section**

### **Synthesis of BP**

Bulk BP is synthesized through a facile high-energy ball milling method. Red phosphorus (RP) powder (Alfa Aesar, 99.99%, 800 mg) and stainless steel balls (11, 10 mm in diameter; 10, 6 mm in diameter; 20, 2 mm in diameter) were put into a stainless steel vessel (50 mL) and sealed in an argon-filled glove box. The milling process was carried out with a rotation rate of 1200 rpm for 2 h using the high-energy ball milling Instrument (MSK-SFM-LN-192, Hefei Kejing Co. Ltd). This procedure is applied to transform RP into BP.

### **Synthesis of c-CN**

Conductive c-CN material is synthesized by a “molten salt reduction denitrifying” route from pristine g-C<sub>3</sub>N<sub>4</sub>. The pristine g-C<sub>3</sub>N<sub>4</sub> is first prepared by a simple calcination method according to our previous work.<sup>1</sup> Then, the obtained g-C<sub>3</sub>N<sub>4</sub>, Mg powder, and AlCl<sub>3</sub> were homogeneously mixed and loaded in a stainless-steel autoclave and heated at 200 °C for 10h. After cooling to room temperature naturally, the collected precipitate was put in 0.1 M hydrochloric acid and stirred for several hours. Afterward, the product was washed with distilled water and ethanol until the solution was neutral. Finally, the product was dried in a vacuum at 60 °C overnight for further use.

### **Synthesis of BP/c-CN**

BP/c-CN hybrid is synthesized by a facile ball-milling process. The as-prepared bulk BP and c-CN were mixed with a mass ratio of 20:1. The mixed powder and stainless-steel balls (10, 10 mm in diameter; 10, 6 mm in diameter; 20, 2 mm in diameter) are placed in a stainless-steel jar (50 mL) and sealed in a glovebox under Ar atmosphere. The container is mounted on a high-energy ball milling device (MSK-SFM-LN-192, Hefei Kejing Co. Ltd), followed by ball-milling for 2h at a speed of 1000 rpm.

### **Computational Method**

The density functional theory computations were carried out by the Vienna ab initio simulation package (VASP) using the projector augmented wave (PAW) method.<sup>2-4</sup> The exchange-correlation potential was represented by the Perdew–Burke–Ernzerhof (PBE) functional within the generalized gradient approximation (GGA).<sup>5</sup> The black phosphorus (010) and graphene (001) surfaces were used to construct the BP@C heterostructure, which has good lattice matching. The cutoff energy is set to 500 eV. The structures were relaxed until the convergence tolerances of energy and force were less than  $1.0 \times 10^{-5}$  eV/atom and  $3.0 \times 10^{-2}$  eV/Å. The  $k$ -point sampling grid is set to  $3 \times 3 \times 1$ . The vacuum layer is 15 Å. The DFT-D3 method is used to describe the van der Waals interaction.<sup>6</sup> And, the adsorption energy ( $E_{\text{ad}}$ ) of the H atom on BP or BP@C was calculated by:

$$E_{\text{ad}} = E(\text{sub} + \text{H}) - E(\text{sub}) - 1/2E(\text{H}_2) \quad (1)$$

Where  $E(\text{sub} + \text{H})$ ,  $E(\text{sub})$ , and  $E(\text{H}_2)$  are the energy of H-adsorbed BP or BP@C, BP or BP@C, and an H<sub>2</sub> gas molecule, respectively.

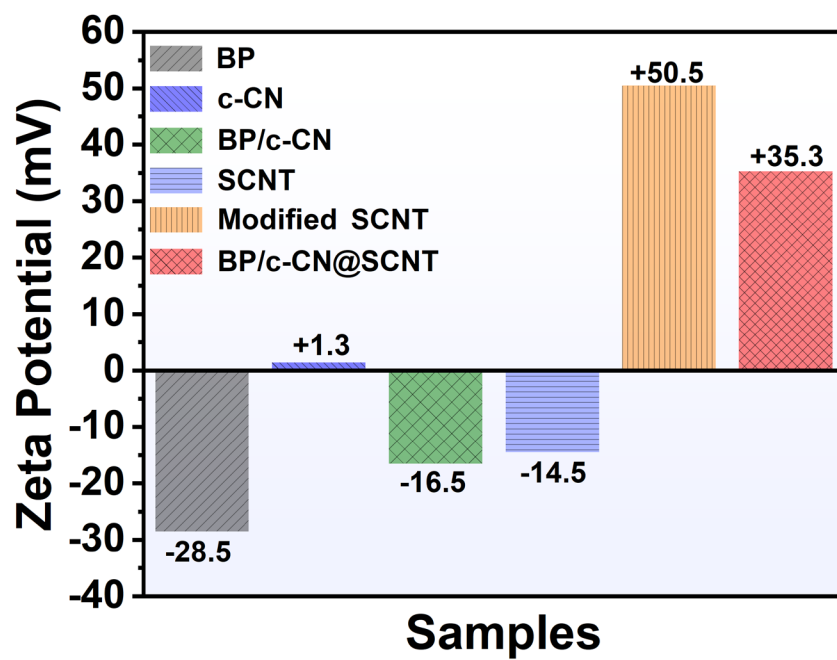
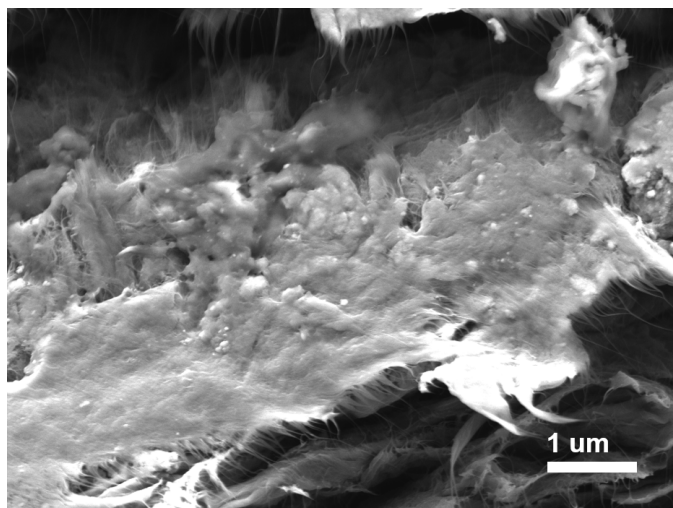
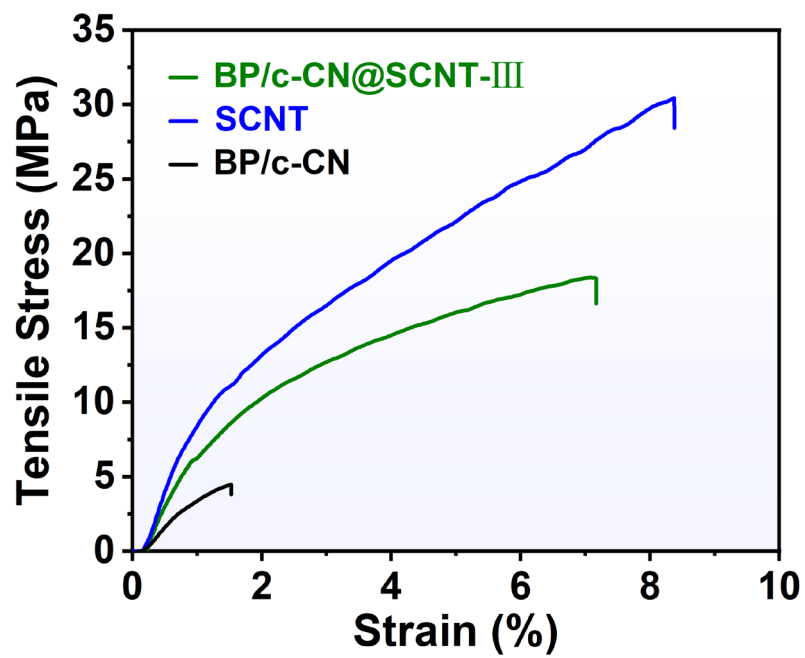


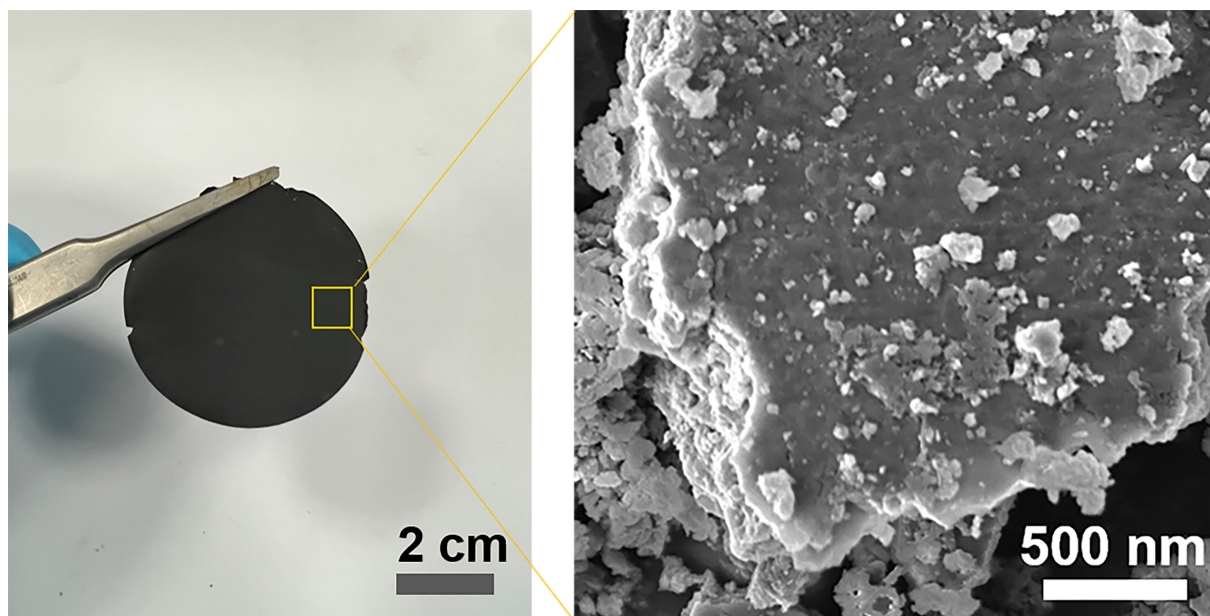
Fig. S1 Zeta potential of all samples.



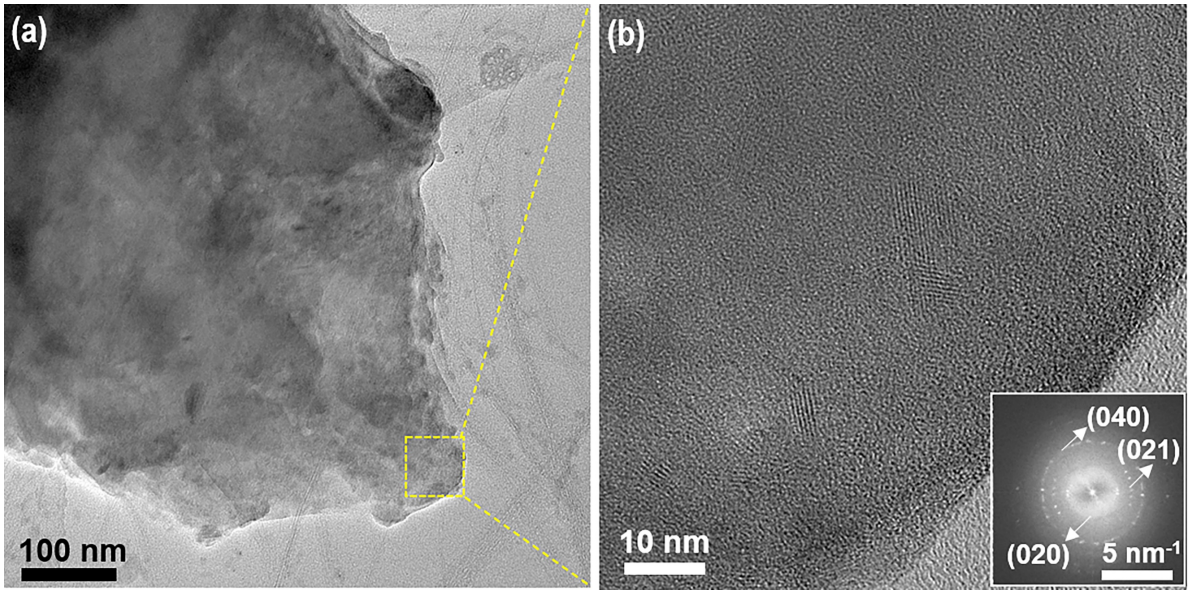
**Fig. S2** The cross-section of the BP/c-CN@SCNT film.



**Fig. S3** Stress-strain curves of BP/c-CN, SCNT, and BP/c-CN@SCNT-III films.

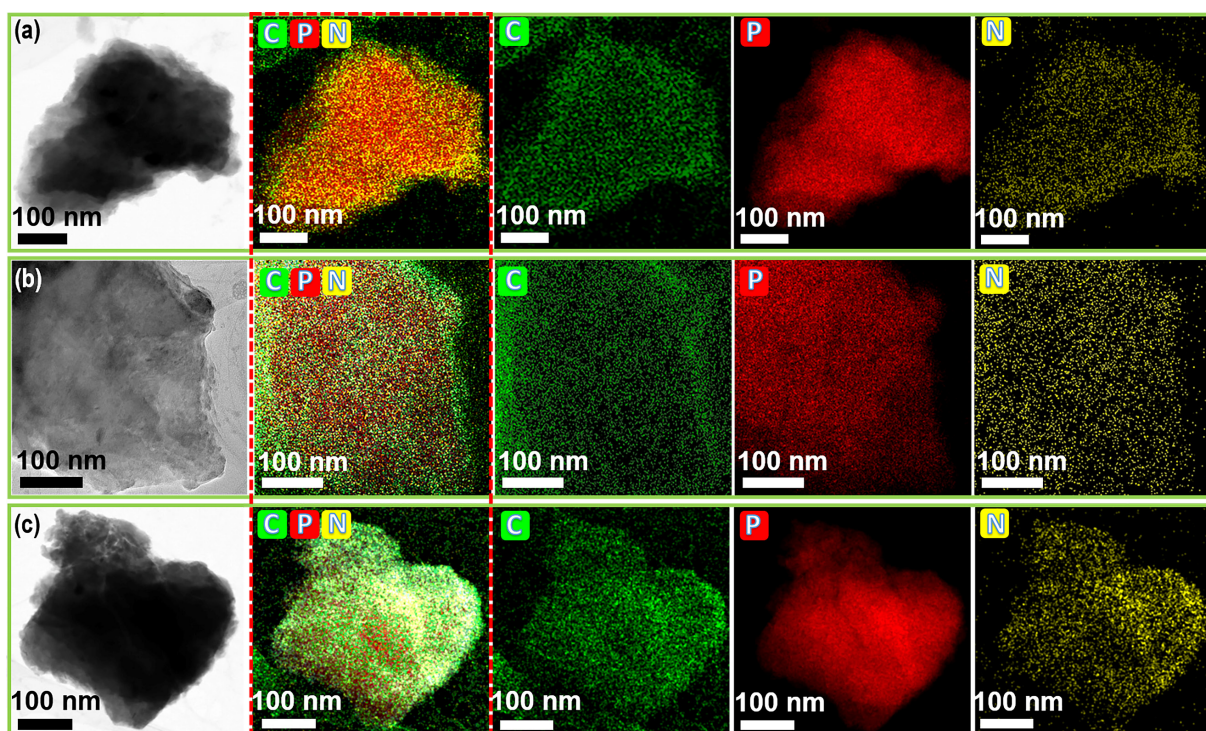


**Fig. S4** Optical and SEM image of the pristine BP/c-CN film.



**Fig. S5** (a) TEM, and (b) HRTEM images of BP/c-CN@SCNT-III sample (inset in panel b is the electron diffraction pattern).





**Fig. S6** EDS elemental mapping images of (a) BP/c-CN@SCNT-IV, (b) BP/c-CN@SCNT-III, and (c) BP/c-CN@SCNT-I.

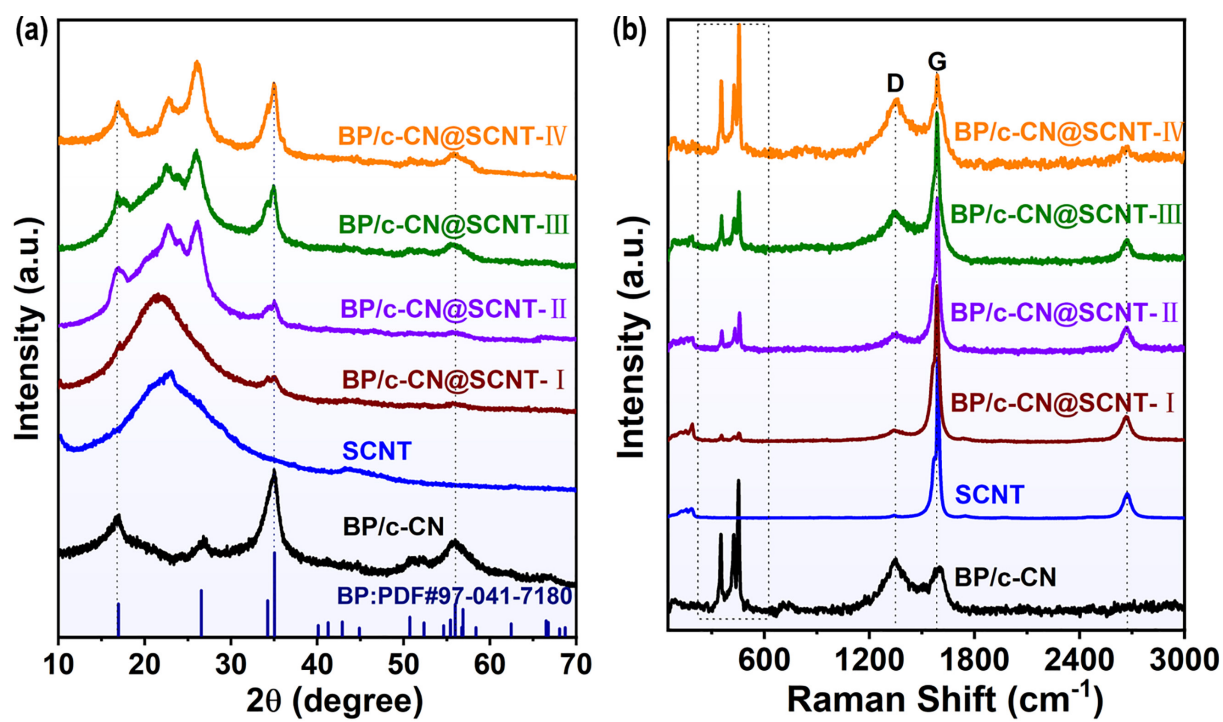
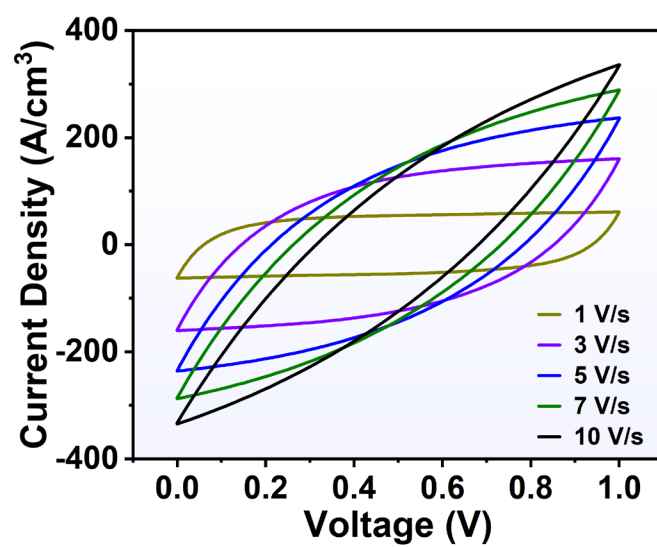


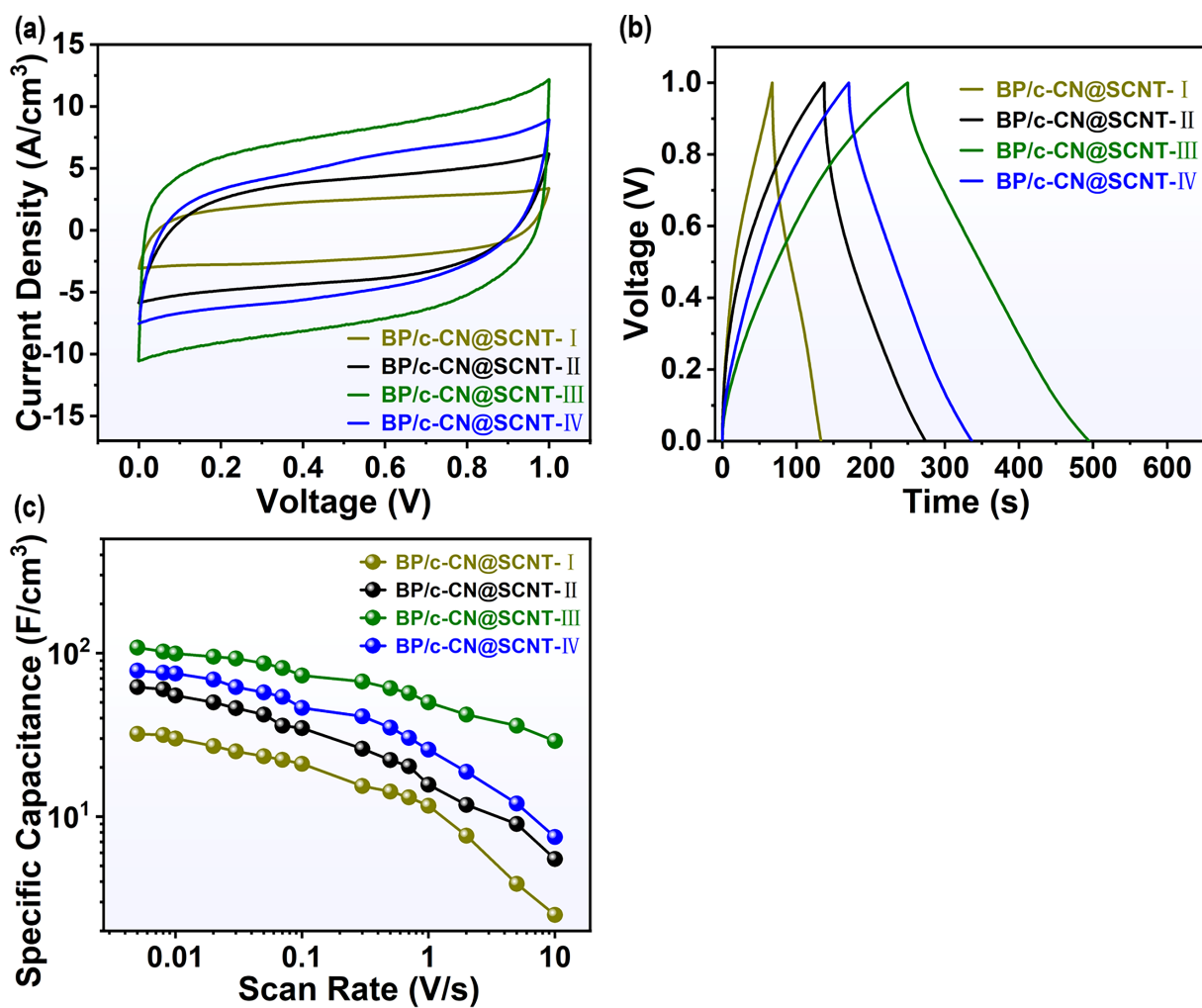
Fig. S7 (a) XRD pattern, and (b) Raman spectra of all samples.

**Table S1** The thickness of the as-perpared film electrodes

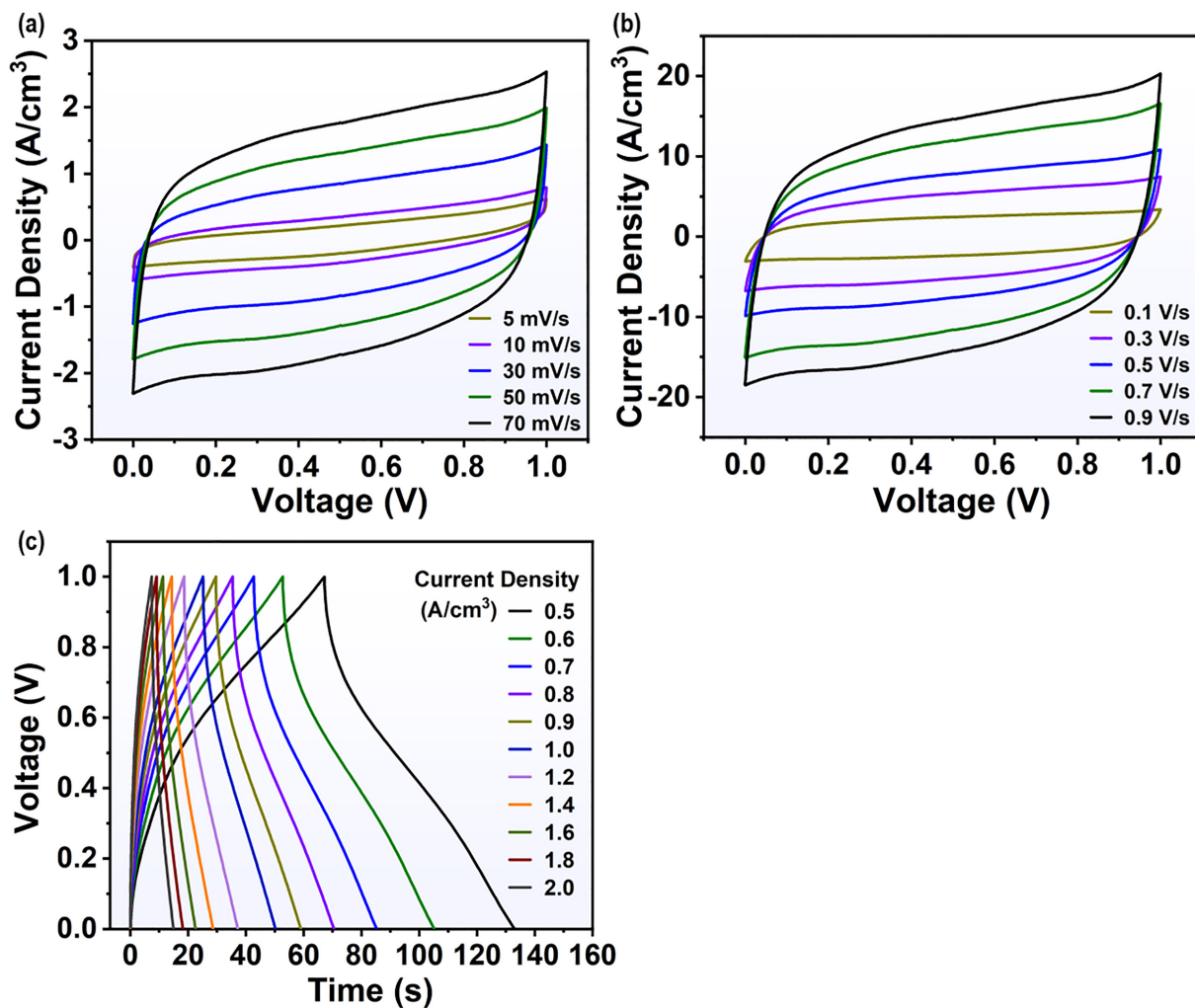
<b>Samples</b>	<b>Thickness (<math>\mu\text{m}</math>)</b>
BP/c-CN	4.9
BP/c-CN@SCNT-IV	4.8
BP/c-CN@SCNT-I	5.5
SCNT	5.0



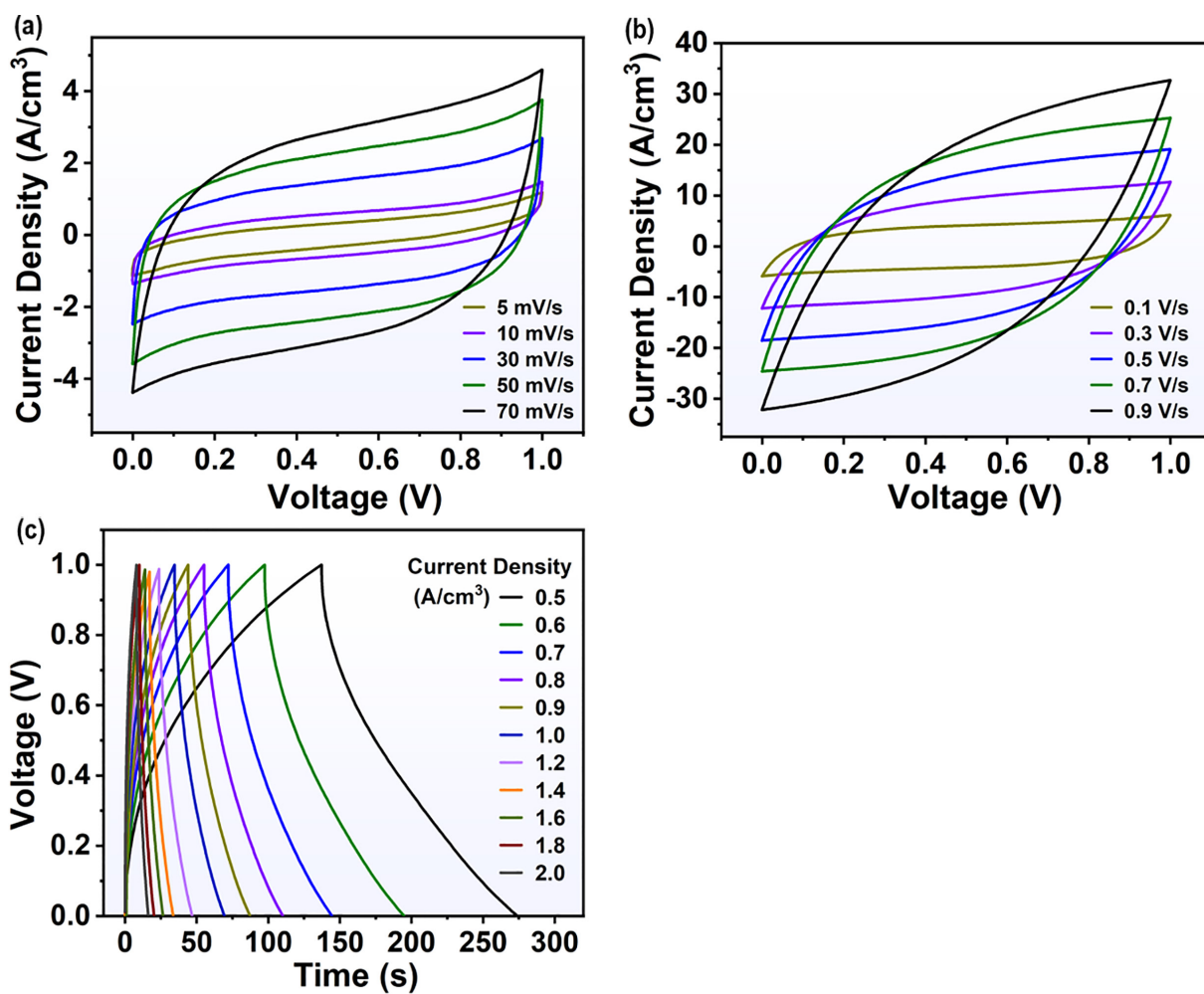
**Fig. S8** CV curves at scan rates from 1 to 10 V/s of the BP/c-CN@SCNT-III film-based FSC.



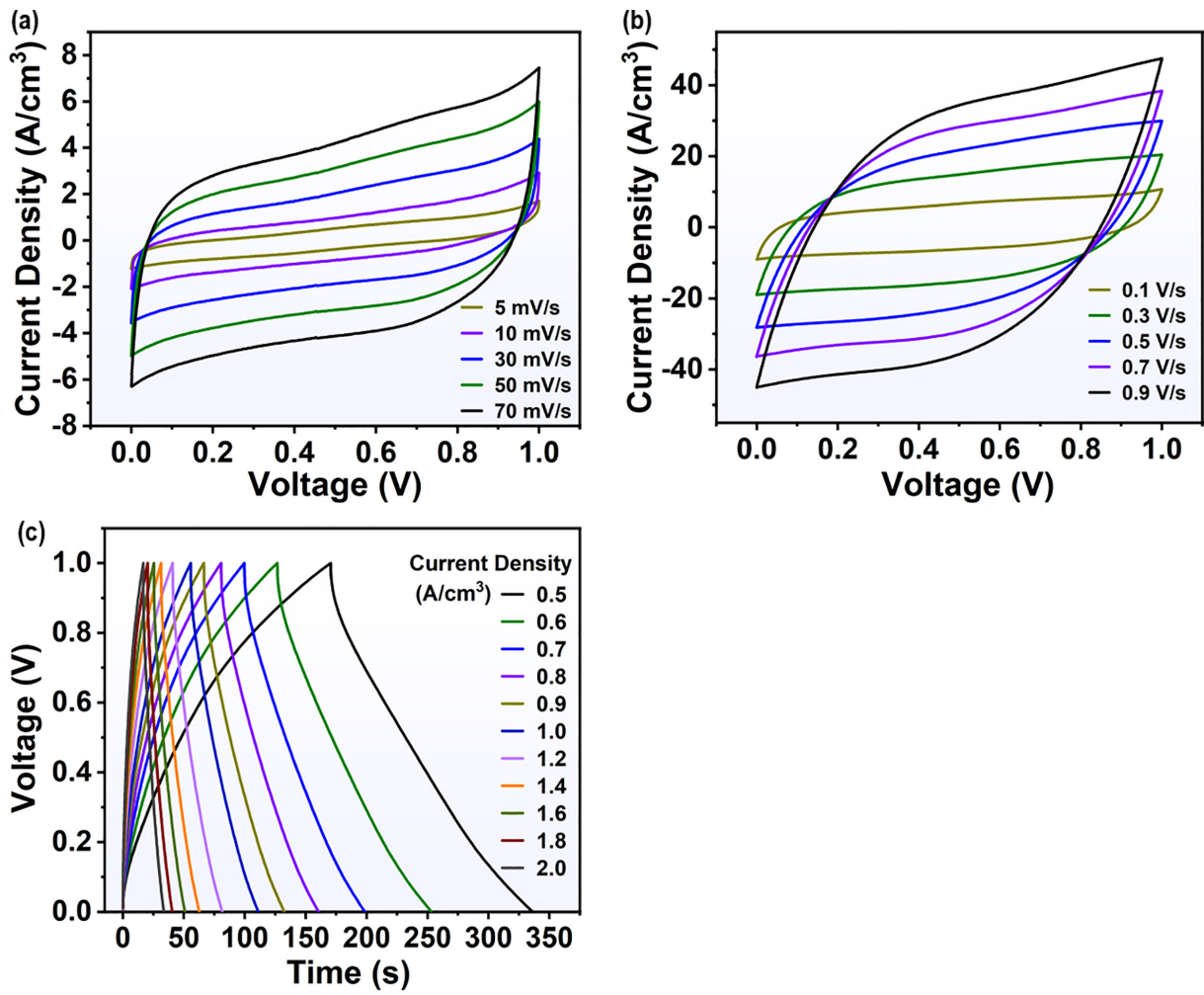
**Fig. S9** (a) CV curves at the scan rate of 100 mV/s, (b) GCD curves at the current density of 0.5 A/g, and (c) The calculated specific capacitances under different scan rates of devices based on BP/c-CN@SCNT-I, BP/c-CN@SCNT-II, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-IV.



**Fig. S10** (a, b) CV curves at various scan rates from 5 to 900 mV/s, and (c) GCD curves of BP/c-CN@SCNT-I film-based FSC.



**Fig. S11** (a, b) CV curves at various scan rates from 5 to 900 mV/s, and (c) GCD curves of BP/c-CN@SCNT-II film-based FSC.

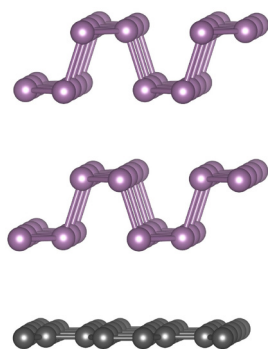


**Fig. S12** (a, b) CV curves at various scan rates from 5 to 900  $\text{mV}/\text{s}$ , and (c) GCD curves of BP/c-CN@SCNT-IV film-based FSC.

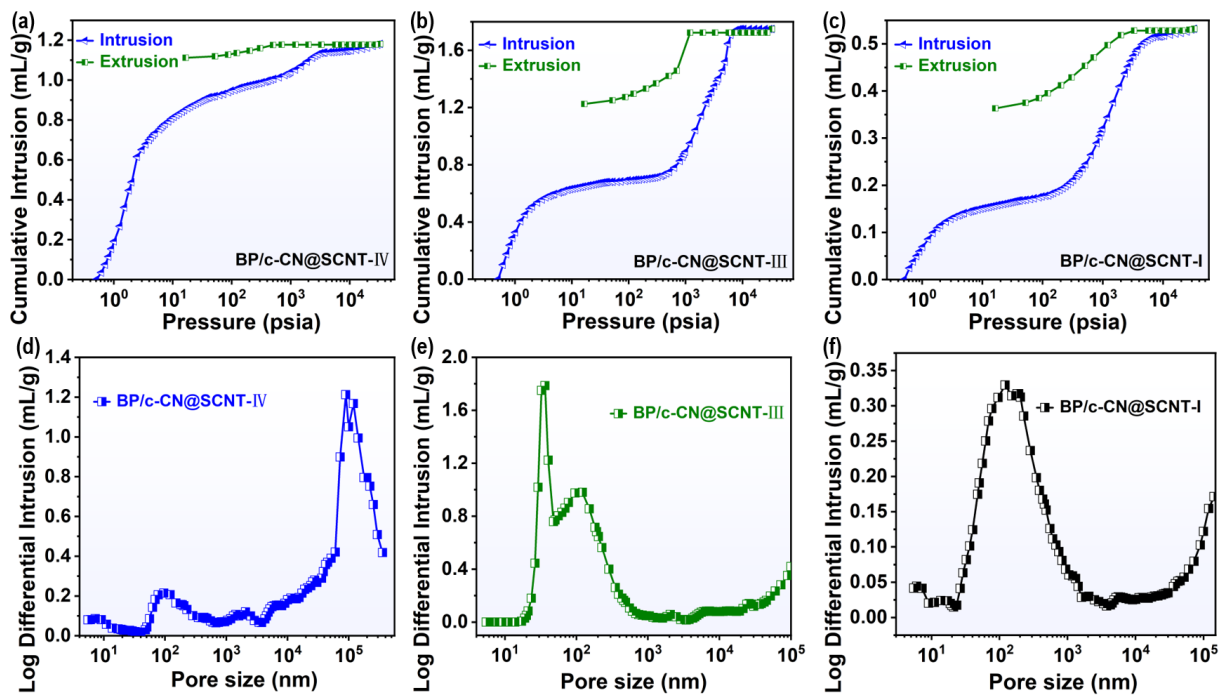


**Table S2** The electrical conductivity of the samples obtained from the “four-probe method”.

<b>Samples</b>	<b>Conductivity (S/m)</b>
BP/c-CN	32
BP/c-CN@SCNT-IV (BP/CN: SCNT=30:1)	210
BP/c-CN@SCNT-III (BP/CN: SCNT=15:1)	877
BP/c-CN@SCNT-I (BP/CN: SCNT=1:1)	1250
SCNT	2150



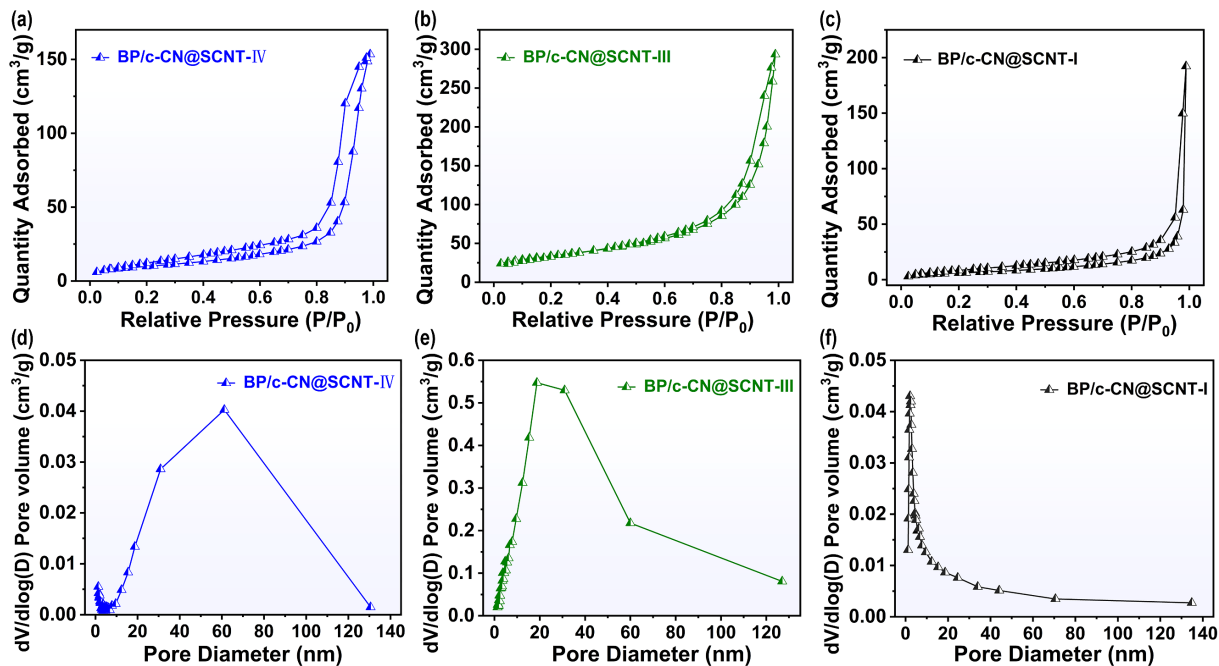
**Fig. S13** The simplified configurational model of the BP@C interface.



**Fig. S14** (a-c) Mercury intrusion-extrusion cycles for the BP/c-CN@SCNT-IV, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-I film, respectively. The pore size distributions of (d) BP/c-CN@SCNT-IV, (e) BP/c-CN@SCNT-III, and (f) BP/c-CN@SCNT-I films obtained from MICP tests.

**Table S3** Structural pore parameters of BP/c-CN@SCNT-IV, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-I films obtained from MICP tests.

Samples	Total pore area (m <sup>2</sup> /g)	Total intrusion volume (mL/g)	Porosity (%)	Average pore diameter (A) (nm)
BP/c-CN@SCNT-IV	19.36	0.53	26.26	214.93
<b>BP/c-CN@SCNT- III</b>	<b>66.83</b>	<b>1.75</b>	<b>59.80</b>	<b>38.30</b>
BP/c-CN@SCNT- I	21.98	1.18	35.90	109.94



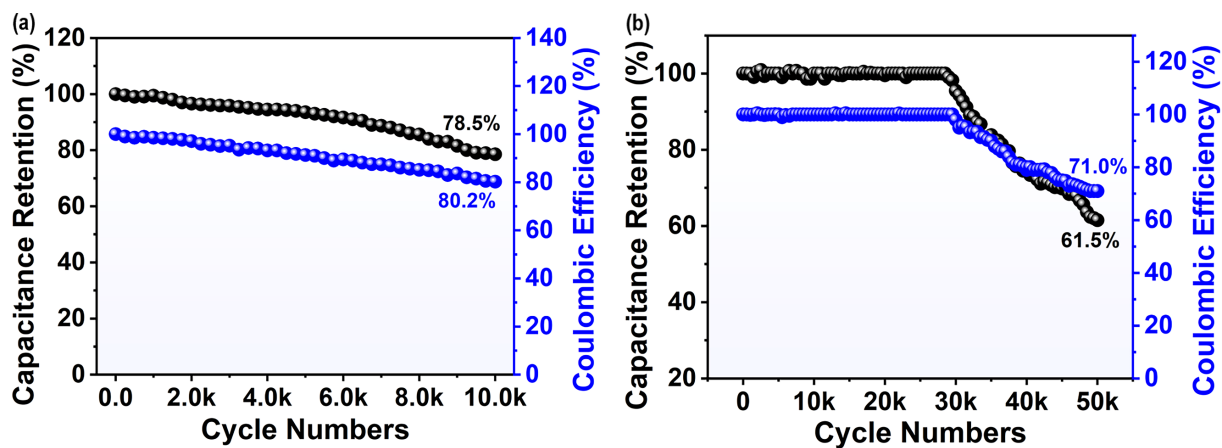
**Fig. S15** (a-c) N<sub>2</sub> adsorption/desorption isotherms of the BP/c-CN@SCNT-IV, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-I films, respectively. (d-f) The BJH pore size distribution of BP/c-CN@SCNT-IV, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-I films, respectively.

**Table S4** Structural pore parameters of BP/c-CN@SCNT-IV, BP/c-CN@SCNT-III, and BP/c-CN@SCNT-I films obtained from N<sub>2</sub> adsorption/desorption measurements.

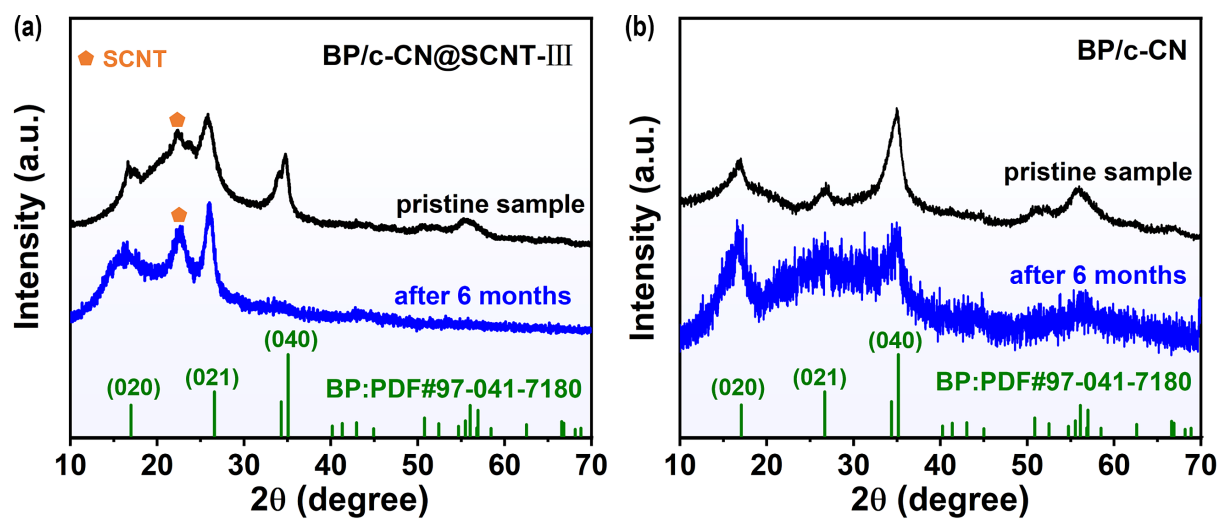
Samples	BET surface area (m <sup>2</sup> /g)	Pore volume (cm <sup>3</sup> /g)	Average pore diameter (nm)
BP/c-CN@SCNT-IV	38.94	0.14	63.93
<b>BP/c-CN@SCNT- III</b>	<b>113.40</b>	<b>0.72</b>	<b>18.76</b>
BP/c-CN@SCNT- I	52.06	0.36	1.35

**Table S5** Specific capacitance and cycling ability of our FSC compared with other BP-based supercapacitors.

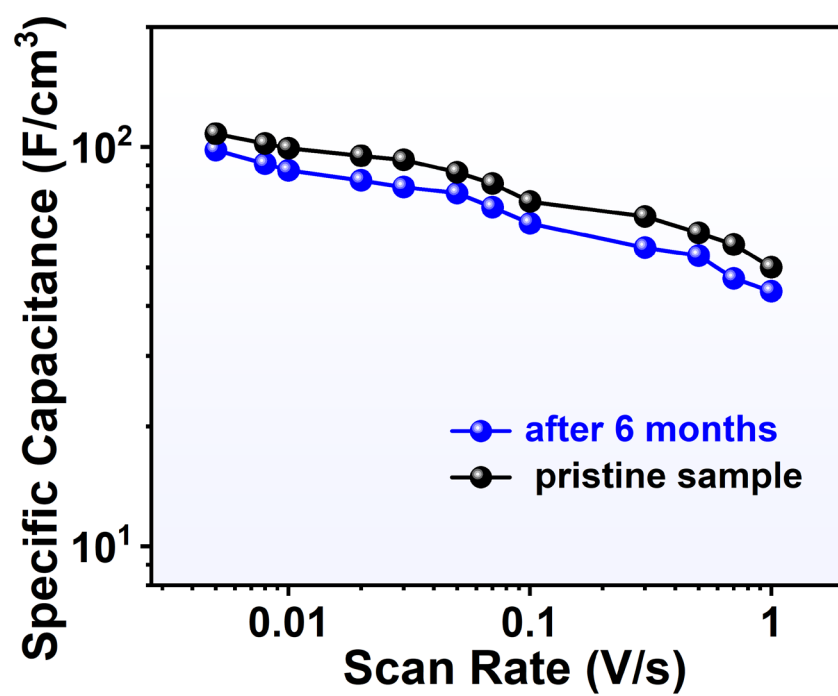
Works	Material	Specific capacitance	Electrolyte	Cycle ability
<b>This work</b>	<b>BP/c-CN@SCNT</b>	<b>108 F/cm<sup>3</sup> at 0.005 V/s</b>	<b>PVA/H<sub>3</sub>PO<sub>4</sub></b>	<b>100% after 50 000 cycles</b>
				84.5% after 10 000 cycles
Ref. 8	BP Nanoflakes	14.5 F/cm <sup>3</sup> at 0.01 V/s	PVA/H <sub>3</sub> PO <sub>4</sub>	71.8% after 30 000 cycles
Ref. 9	BP/CNTs	41.1 F/cm <sup>3</sup> at 0.005 V/s	PVA/H <sub>3</sub> PO <sub>4</sub>	91.5% after 10 000 cycles
Ref. 11	BP/Polyaniline	354 F/g at 0.3 A/g	H <sub>2</sub> SO <sub>4</sub>	96% after 175 cycles
Ref. 12	BP/Polypyrrole	7.7 F/cm <sup>3</sup> at 0.5 A/g	PVA/H <sub>3</sub> PO <sub>4</sub>	99% after 10 000 cycles
Ref. 42	BP sponge	80 F/g at 0.01 V/s	PVA/H <sub>3</sub> PO <sub>4</sub>	80.0% after 15 000 cycles
Ref.43	CNT/MnO <sub>2</sub> -BP	441.7 F/cm <sup>3</sup> at 0.01 V/s	PVA/KOH	90.5% after 10 000 cycles
Ref. 44	BP-CNTs	308.7 F cm <sup>-3</sup> at 0.1 A/cm <sup>3</sup>	EMIMBF <sub>4</sub> /P VDF-HFP	90.2% after 10 000 cycles
Ref.45	BP/Mxene	896.87 F/cm <sup>3</sup> at 0.69 A/cm <sup>3</sup>	PVA/H <sub>2</sub> SO <sub>4</sub>	91.74% after 10 000 cycles
Ref.46	BP/Mxene	361.9 F/cm <sup>3</sup> at 0.1 V/s	Na <sub>2</sub> SO <sub>4</sub> /CM C	90.9% after 40 000 cycles
Ref.47	BP/Polypyrrole	417 F/g at 0.2 A/g	EMI-TFSI	87% after 10 000 cycles



**Fig. S16** Cycling stability and coulombic efficiency at a current density of 1.0 A/cm<sup>3</sup> for (a) BP-based FSC and (b) BP/c-CN-based FSC.

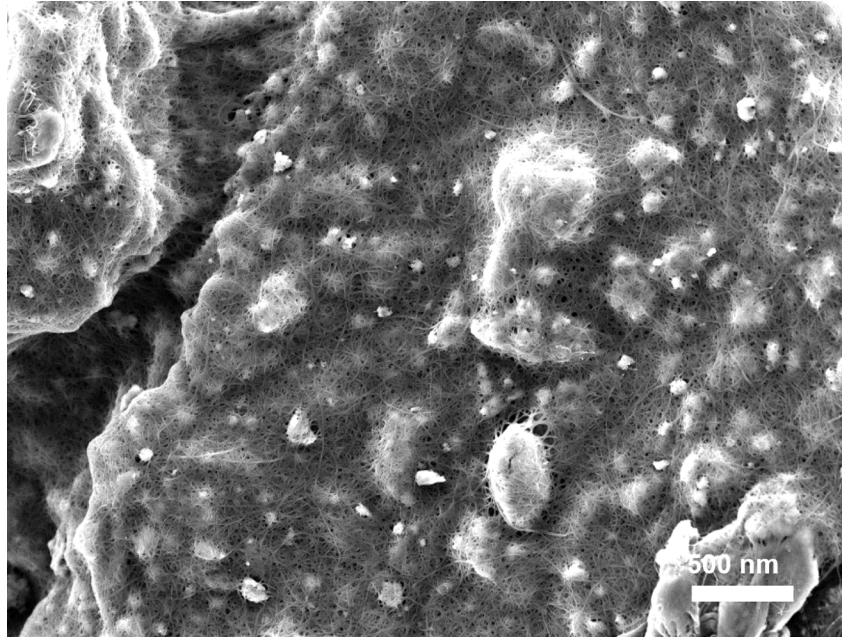


**Fig. S17** XRD images of (a) BP/c-CN@SCNT-III and (b) BP/c-CN after 6 months under ambient conditions.

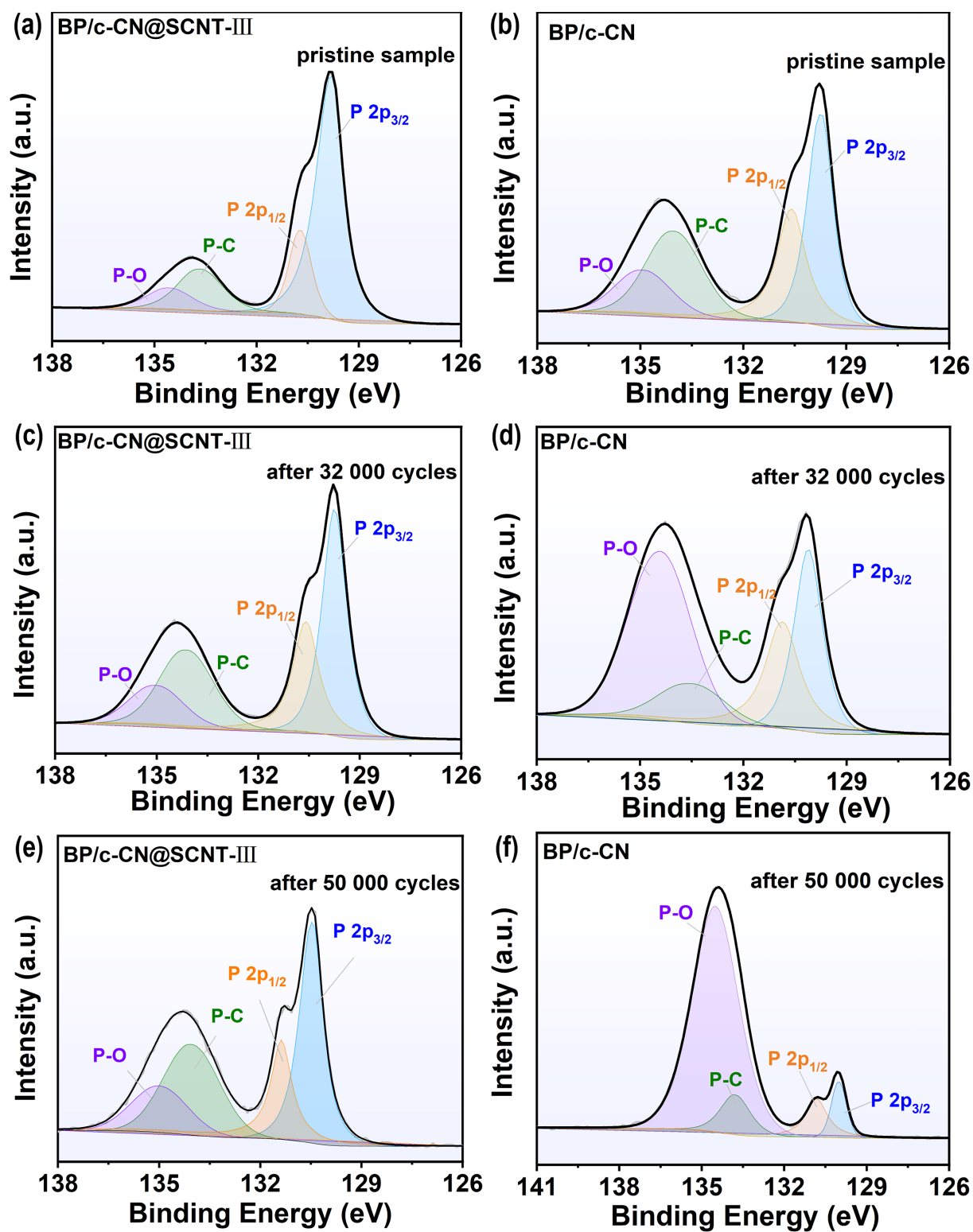


**Fig. S18** Specific capacitance at various scan rates of BP/c-CN@SCNT-III after 6 months under ambient conditions.





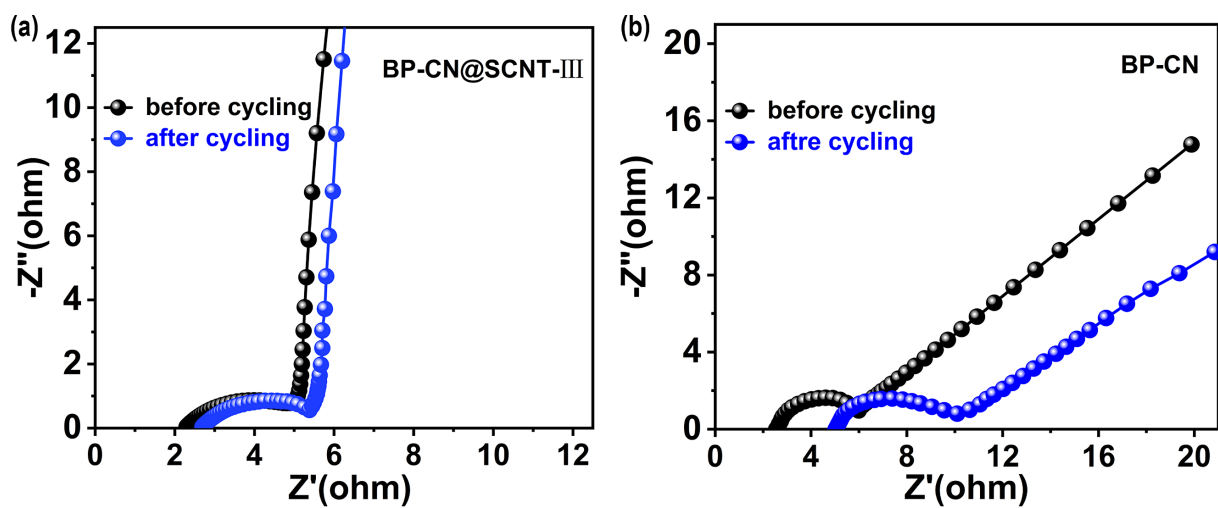
**Fig. S19** SEM image of the BP/c-CN-III film after 50 000 cycling tests.



**Fig. S20** High-resolution P 2p XPS spectra of (a, c, e) BP/c-CN@SCNT-III, and (b, d, f) BP/c-CN after different cycles.

**Table S6.** High-resolution P2p XPS analysis of BP/c-CN@SCNT-III and BP/c-CN samples after different cycles.

Bonding type		P-C	P-O	P2p <sub>3/2</sub>	P2p <sub>1/2</sub>
Sample		/at%	/at%	/at%	/at%
	Pristine sample	16.5	11.6	55.9	16.0
BP/c-CN@SCNT-III	After 32 000 cycles	20.0	16.50	46.5	17.0
	After 50 000 cycles	21.8	17.7	44.5	16.0
	Pristine sample	19.9	17.1	47.2	15.8
BP/c-CN	After 32 000 cycles	14.9	42.7	25.1	17.3
	After 50 000 cycles	8.9	76.9	6.0	8.2



**Fig. S21** Nyquist plots of (a) BP/c-CN@SCNT-III and (b) BP/c-CN film-based device before and after 50 000 cycles.

## Reference

1. M. Shi, T. Wu, X. Song, J. Liu, L. Zhao, P. Zhang and L. Gao, *J. Mater. Chem. A*, 2016, **4**, 10666-10672.
2. G. Kresse and D. Joubert, *Phys. Rev. B*, 1999, **59**, 1758.
3. G. Kresse and J. Furthmüller, *Comp.Mater. Sci.*, 1996, **6**, 15-50..
4. G. Kresse and J. Furthmüller, *Phys. Rev. B*, 1996, **54**, 11169.
5. J. P. Perdew, K. Burke and M. Ernzerhof, *Phys. Rev. Lett.*, 1996, **77**, 3865.
6. K. Lee, É. D. Murray, L. Kong, B. I. Lundqvist and D. C. Langreth, *Phys. Rev. B*, 2010, **82**, 081101.